Low frequencies to 40 GHz Phase Modulators

MODULATOR



of electro-optic phase modulators available on the market for the 1550 nm wavelength band.

The MPX-LN and MPZ-LN series make up the most comprehensive range

- The MPZ-LN series are ideally suited for high bandwidth operation at 1 GHz, 10 GHz, 20 GHz and up to 40 GHz.
- The MPX-LN-0.1 has a high impedance input optimized for modulation frequencies below 150 MHz.

Designed using state-of-the-art and proven lithium niobate technology, MPX-LN and MPZ-LN phase modulators are easy to operate and to integrate. They offer the highest performance for a wide range of applications from laboratory experiments to demanding industrial systems.

- · Low and wide electro-optical bandwidth
- C & L bands

FEATURES

- Low insertion loss
- Low Vπ

APPLICATIONS

- · Side bands generation
- Interferometric sensing
- Frequency shifting / broadening
- · Quantum key distribution
- High data rate telecommunications
- Laser combining
- Pound-Drever-Hall locking (PDH)

OPTIONS

- Low residual intensity modulation
- Low insertion loss
- High electrical input power capability

RELATED EQUIPMENTS

- Matched RF amplifiers
- MX, MXAN, MXER Amplitude modulators
- Short optical pulse ModBox

Low and Medium Bandwidth Phase Modulators - Highlights

Parameter	MPX-LN-0.1	MPZ-LN-01		
Operating wavelength	1530 nm - 1625 nm			
Electro-optical bandwidth	150 MHz	1.5 GHz		
Vπ RF @50 kHz	3.5 V	3 V		
Insertion loss	2.7 dB	2.5 dB		

Specifications given at 25 °C, 1550 nm.

Wide Bandwidth Phase Modulators - Highlights

Parameter	MPZ-LN-10 MPZ-LN-20 MPZ-LN-4					
Operating wavelength	1530 nm - 1625 nm					
Electro-optical bandwidth	12 GHz 25 GHz 33 G					
Vπ RF @50 kHz	4 V 4.5 V 6V					
Insertion loss	2.5 dB	2.5 dB	2.5 dB			

Specifications given at 25 °C, 1550 nm.

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Modulator

MPX-LN-0.1

150 MHz Phase Modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Electro-optic bandwidth	S ₂₁	-	-	150	-	MHz
Vπ RF @50 kHz	Vπ RF _{50 kHz}	-	-	3.5	4	V
RF input impedance	Z _{in-RF}	-	-	10 000	-	Ω

Optical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Waveguide process	-	-	Ti diffusion			
Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without optical connectors	-	2.7	3.5	dB
Polarization dependent loss	PDL	-	-	5	8	dB
Optical return loss	ORL	-	-40	-45	-	dB

All specifications given at 25 $^{\circ}$ C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Modulation voltage range	EV _{in}	-20	20	V
Optical input power	OP _{in}	-	20	dBm
Operating temperature	ОТ	0	+70	°C
Storage temperature	ST	-40	+85	°C



Low frequencies to 40 GHz Phase Modulators

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MPZ-LN-01
1 GHz Phase Modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Electro-optic bandwidth	S ₂₁	-	1	1.5	-	GHz
Ripple S ₂₁	ΔS ₂₁	-	-	0.5	-	dB
Electrical return loss	S ₁₁	-	-	-15	-12	dB
Vπ RF @50 kHz	VπRF _{50 kHz}	-	-	3	3.5	V
Vπ RF @1 GHz	VπRF _{1 GHz}	-	-	3.1	3.6	V
Impedance matching	Z _{in-RF}	-	-	50	-	Ω

Optical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Crystal	-	-	Lithium Niobate Z-Cut, X-Prop			
Waveguide process	-	-	Ti diffusion			
Operating wavelength	λ	-	1530	1550	1570	nm
Insertion loss	IL	Without connectors	-	2.5	3.5	dB
Optical return loss	ORL	-	-40	-45	-	dB

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
RF input power	EP _{in}	-	33	dBm
Optical input power	OP _{in}	-	20	dBm
Operating temperature	ОТ	0	+70	°C
Storage temperature	ST	-40	+85	°C

Low frequencies to 40 GHz Phase Modulators

MODULATOR

MPZ-LN-10

10 GHz Phase Modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Electro-optic bandwidth	S ₂₁	RF electrodes, from 2 GHz	10	12	-	GHz
Ripple S ₂₁	ΔS ₂₁	-	-	0.5	1	dB
Electrical return loss	S ₁₁	-	-	-17	-14	dB
Electrical return loss - HEP option	S ₁₁	-	-	-14	-10	dB
Vπ RF @50 kHz	VπRF _{50 kHz}	-	-	4	5	V
Vπ RF @10 GHz	VπRF _{10 GHz}	-	-	6	7	V
Impedance matching	Z _{in-RF}	-	-	50	-	Ω

Optical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Crystal	-	-	Lithium Niobate Z-Cut Y-Prop				
Waveguide process	-	-	Ti diffusion				
Operating wavelength	λ	-	1530	1550	1625	nm	
Insertion loss	IL	Without optical connectors	-	2.5	3.5	dB	
Low insertion loss option	LIL	Without optical connectors	-	2	2.5	dB	
Optical return loss	ORL	-	-40	-45	-	dB	

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
RF input power	EP _{in}	-	28	dBm
High electrical input power option	HEP _{in}	-	33	dBm
Optical input power	OP_in	-	20	dBm
Operating temperature	ОТ	0	+70	°C
Storage temperature	ST	-40	+85	°C

Low frequencies to 40 GHz Phase Modulators

MODULATOR

MPZ-LN-20 20 GHz Phase Modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Electro-optic bandwidth	S ₂₁	RF electrodes, from 2 GHz	20	25	-	GHz
Ripple S ₂₁	ΔS ₂₁	-	-	0.5	1	dB
Electrical return loss	S ₁₁	-	-	-12	-10	dB
Vπ RF @50 kHz	Vπ RF _{50 kHz}	-	-	4.5	5.5	V
Vπ RF @20 GHz	Vπ RF _{20 GHz}	-	-	6.5	7.5	V
Impedance matching	Z _{in-RF}	-	-	50	-	Ω

Optical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Crystal	-	-		Lithium Nioba	te Z-Cut Y-Prop	
Waveguide process	-	-		Ti diff	fusion	
Operating wavelength	perating wavelength λ -		1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	2.5	3	dB
Optical return loss	ical return loss ORL -		-40	-45	-	dB

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
RF input power	EP _{in}	-	28	dBm
Optical input power	OP _{in}	-	20	dBm
Operating temperature	ОТ	0	+70	℃
Storage temperature	ST	-40	+85	°C

Low frequencies to 40 GHz Phase Modulators

MODULATOR

MPZ-LN-40 40 GHz Phase Modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Electro-optic bandwidth	S ₂₁	RF electrodes, from 2 GHz	30	33	-	GHz
Ripple S ₂₁	ΔS ₂₁	-	-	0.5	1	dB
Electrical return loss	S ₁₁	-	-	-12	-10	dB
Vπ RF @50 kHz	Vπ RF _{50 kHz}	-	-	6	7	V
Vπ RF @30 GHz	Vπ RF _{30 GHz}	-	-	8.5	10	V
Impedance matching	Z _{in-RF}	-	-	50	-	Ω

Optical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Crystal	-	-		Lithium Nioba	te Z-Cut Y-Prop	
Waveguide process	-	-		Ti diff	fusion	
Operating wavelength λ -		-	1530	1550	1625	nm
Insertion loss	n loss IL Without connectors		-	2.5	3	dB
Optical return loss	ical return loss ORL -		-40	-45	-	dB

All specifications given at 25 °C, 1550 nm, unless differently specified.

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
RF input power	EP _{in}	-	28	dBm
Optical input power	OP _{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

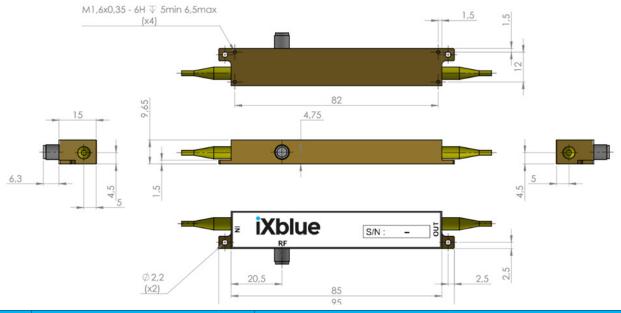


Low frequencies to 40 GHz Phase Modulators

Modulator

Mechanical Diagram and Pinout

All measurements in mm



Port	Function	Note		
IN	Optical input port	Polarization maintaining 1550 nm Corning PM 15-U25D length : 1.5 meter, buffer diameter : 900 um		
OUT	Optical output port	Polarization maintaining 1550 nm Corning PM 15-U25D length : 1.5 meter, buffer diameter : 900 um		
RF	RF input port	Wiltron female K (V type for MPZ-LN-40)		

Ordering information

-POL

MPX-LN-XX-00-P-P-AB-CD / MPZ-LN-WW-00-P-P-AB-CD -HEP

XX = X-cut Bandwidth: 0.1 150 MHz

WW = Z-cut Bandwidth: 01 01 GHz 10 10 GHz 20 20 GHz 40 40 GHz

P = Single Mode and Polarization Maintaining fiber

AB = Input connector: 00 bare fiber FA FC/APC FC FC/SPC CD = Output connector: 00 bare fiber FA FC/APC FC FC/SPC

POL = Embedded in-line POLarizer

HEP = High Electrical Power option for the MPZ-LN-10 only LIL = Low Insertion Loss option for the MPZ-LN-10 only

Note: optical connectors are Senko with narrow key or equivalent

About us

iXblue Photonics produces specialty optical fibers and Bragg gratings based fiber optics components and provides optical modulation solutions based on the company lithium niobate (LiNbO₃) modulators and RF electronic modules.

iXblue Photonics serves a wide range of industries: sensing and instruments, defense, telecommunications, space and fiber lasers as well as research laboratories all over the world.

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